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IN THE UNITED STATES PATENT AND TRADE MARKS OFFICE

Applicant: Richard C. Foss
Serial No: 08/147,038
Filed: November 4, 1993
Title: DYNAMIC RANDOM ACCESS MEMORY USING
IMPERFECT ISOLATING TRANSISTORS
Art Unit: 2506
Examiner: Tan Dinh
Our File: 243P11US-C2

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October 13, 1994

The Commissioner of Patents
and Trade Marks,
Washington, D.C., 20231
U.S.A.

Dear Sir:

This is in response to the official action dated
July 27th, 1994 in the above-identified application.

Please amend the claims as follows:

6. (Twice amended) A dynamic random access memory
(DRAM) as defined in claim 1, further comprising:
- [(a) a plurality of bit storage capacitors,
 - (b) a folded bit line for receiving charge stored
on one of said capacitors having bit line capacitance,
 - (c) a sense amplifier having a pair of sense nodes
for sensing a voltage differential across said sense nodes,]

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